AUTHOR CORRECTION

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Author Correction: Direct growth of orthorhombic $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ thin films for hysteresis-free MoS_2 negative capacitance field-effect transistors

Hae Won Cho, Pavan Pujar, Minsu Choi, Seunghun Kang, Seongin Hong, Junwoo Park, Seungho Baek, Yunseok Kim, Jaichan Lee and Sunkook Kim

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The original version of this Article contained an error in the Acknowledgements: '2021R1A2B5B0200216' should have read '2021R1A2B5B02002167'. This has now been corrected in both the PDF and HTML versions of the Article.

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